

STP55NF06L STB55NF06L - STB55NF06L-1

N-channel 60V - 0.014Ω - 55A TO-220/D²PAK/I²PAK STripFET™ II Power MOSFET

General features

Туре	V _{DSS}	/ _{DSS} R _{DS(on)}	
STP55NF06L	60V	<0.018Ω	55A
STB55NF06L	60V	<0.018Ω	55A
STB55NF06L-1	60V	<0.018Ω	55A

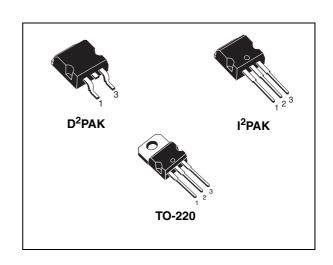
- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Description

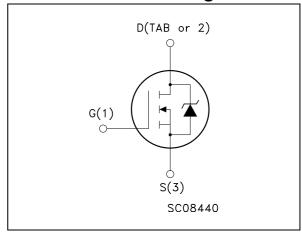
This Power MOSFET is the latest development of STMicroelectronis unique "Single Feature SizeTM" strip-based process. The resulting transistor shows extremely high packing density for low onresistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

■ Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STP55NF06L	P55NF06L	TO-220	Tube
STB55NF06LT4	B55NF06L	D ² PAK	Tape & reel
STB55NF06L-1	STB55NF06L-1 B55NF06L		Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	
3	Test circuit	8
4	Package mechanical data	9
5	Packaging mechanical data	13
6	Revision history	14

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage (V _{GS} = 0)	60	V
V _{GS}	Gate-source voltage	± 16	V
I _D	Drain current (continuous) at T _C = 25°C	55	Α
I _D	Drain current (continuous) at T _C = 100°C	39	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	220	Α
P _{TOT}	Total dissipation at T _C = 25°C	95	W
	Derating factor	0.63	W/°C
dv/dt ⁽²⁾	Peak diode recovery voltage slope	20	V/ns
E _{AS} ⁽³⁾	Single pulse avalanche energy	300	mJ
T _J T _{stg}	Operating junction temperature Storage temperature	-55 to 175	°C

^{1.} Pulse width limited by safe operating area

Table 2. Thermal data

R _{thj-case}	Thermal resistance junction-case max	1.58	°C/W
R _{thj-a}	Thermal resistance junction-ambient max	62.5	°C/W
T _I	Maximum lead temperature for soldering purpose	300	°C

^{2.} $I_{SD} \le 55A$, $di/dt \le 200A/\mu s$, $V_{DD} \le V_{(BR)DSS}$, $T_j \le T_{JMAX}$.

^{3.} Starting $T_j = 25$ °C, $I_D = 27.5A$, $V_{DD} = 30V$

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	60			٧
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = Max rating, V_{DS} = Max rating @125°C			1 10	μ Α μ Α
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ±16V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.7		V
R _{DS(on)}	Static drain-source on resistance	V_{GS} = 5V, I_{D} = 27.5A V_{GS} = 10V, I_{D} = 27.5A		0.016 0.014	0.020 0.018	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} =15V, I _D = 27.5A		30		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} =25V, f=1 MHz, V _{GS} =0		1700 300 105		pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} =48V, I_{D} = 55A V_{GS} =4.5V		27 7 10	37	nC nC nC

^{1.} Pulsed: pulse duration=300µs, duty cycle 1.5%

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time Rise time	V_{DD} =30 V, I_{D} =27.5A, R_{G} =4.5V (see Figure 12)		20 100		ns ns
t _{d(off)}	Turn-off delay time Fall time	V_{DD} =30V, I_{D} =27.5A, R_{G} =4.5V (see Figure 12)		40 20		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I _{SD}	Source-drain current				12	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				48	Α
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 55A, V _{GS} =0			1.6	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 55A, di/dt = 100A/ μ s, V_{DD} = 30V, Tj = 150°C (see Figure 14)		80 200 5		ns nC A

^{1.} Pulse width limited by safe operating area

^{2.} Pulsed: pulse duration=300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Thermal impedance

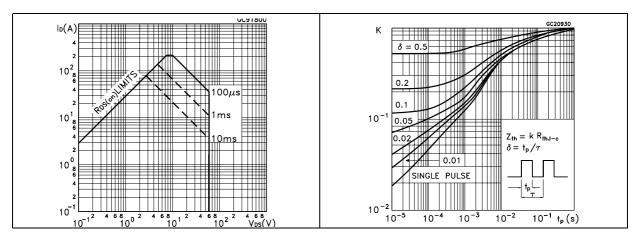


Figure 3. Output characterisics

Figure 4. Transfer characteristics

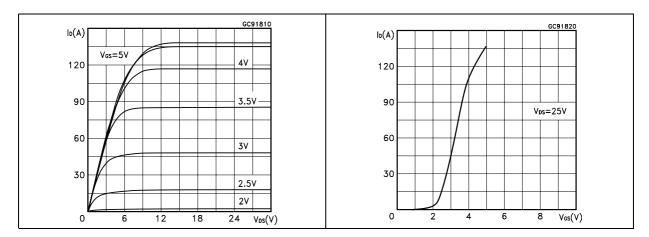
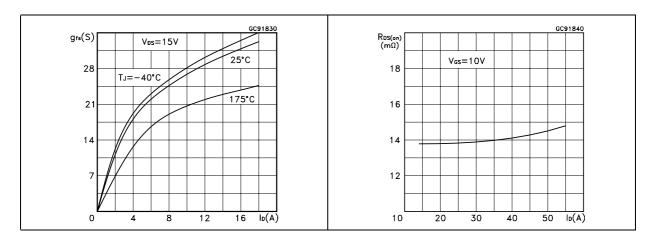


Figure 5. Transconductance

Figure 6. Static drain-source on resistance



6/15

Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

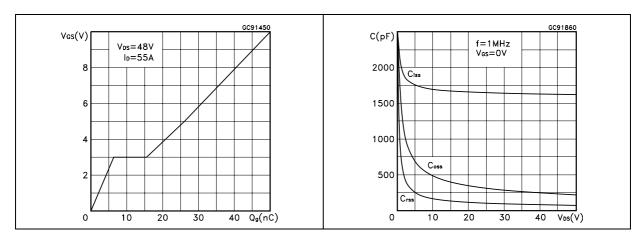


Figure 9. Normalized gate threshold voltage Figure 10. Normalized on resistance vs vs temperature temperature

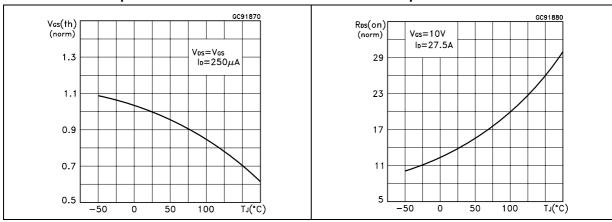
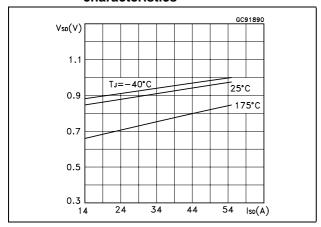


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

Figure 13. Gate charge test circuit

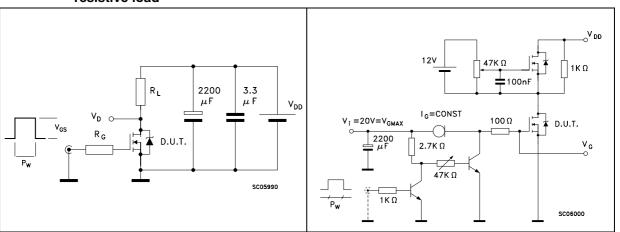


Figure 14. Test circuit for inductive load switching and diode recovery times

Figure 15. Unclamped Inductive load test circuit

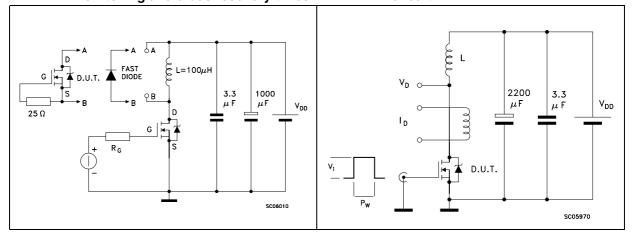
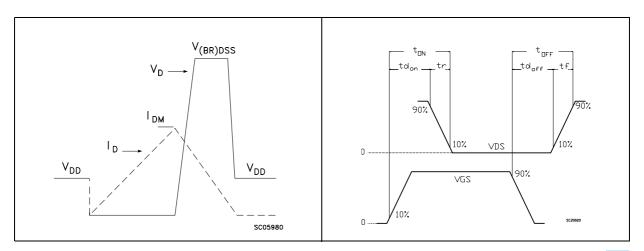


Figure 16. Unclamped inductive waveform

Figure 17. Switching time waveform



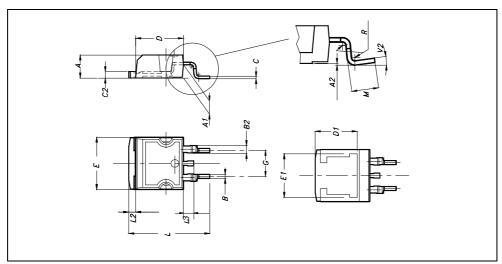
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

9/15

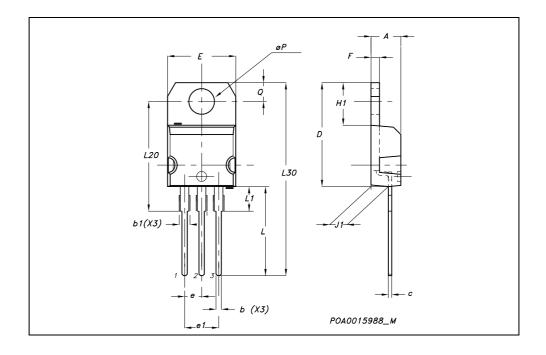
D²PAK MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0₀		4º			



TO-220 MECHANICAL DATA

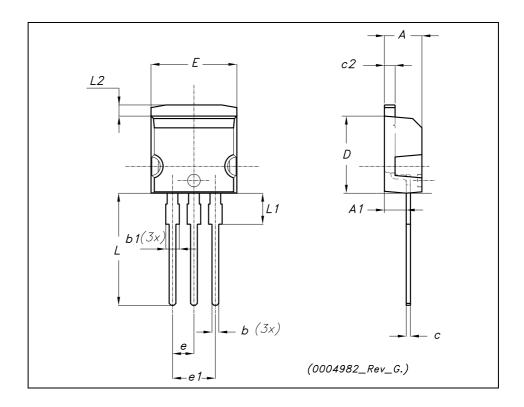
DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
Е	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



47/

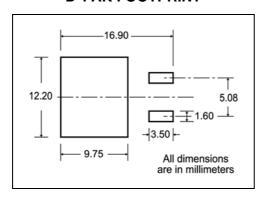
TO-262 (I²PAK) MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
Е	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055

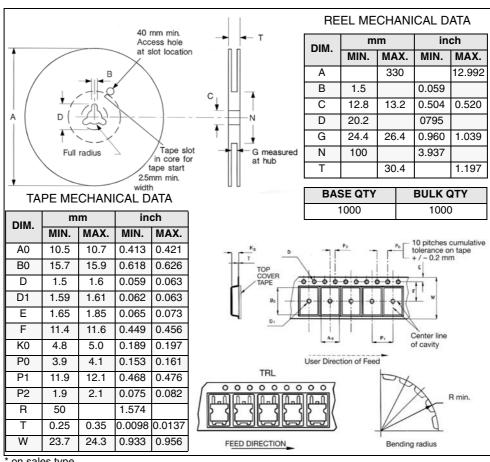


Packaging mechanical data 5

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 7. Revision history

Date	Revision	Changes
09-Sep-2004	3	Complete document
27-Nov-2006	4	The document has been reformatted

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